

Title (en)  
AN ELECTRICALLY CONDUCTING STRUCTURE FOR A LIGHT TRANSMISSIBLE DEVICE

Title (de)  
ELEKTRISCH LEITENDE STRUKTUR FÜR EINE LICHTDURCHLÄSSIGE VORRICHTUNG

Title (fr)  
STRUCTURE ÉLECTROCONDUCTRICE POUR UN DISPOSITIF ÉMETTEUR OPTIQUE

Publication  
**EP 2298032 A4 20120620 (EN)**

Application  
**EP 08741968 A 20080506**

Priority  
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Abstract (en)  
[origin: WO2009136863A1] An electrically conducting structure for a light transmissible device and a method of forming an electrically conducting structure for a light transmissible device are provided. The structure comprises a first transparent conducting material layer formed using first process conditions; at least one other transparent conducting material layer formed directly on the first layer, said at least one other transparent conducting material layer being formed using second process conditions that are different from the first process conditions; and wherein the first layer functions as a buffer layer to reduce adverse effects for the light transmissible device during formation of said at least one other transparent conducting material layer.

IPC 8 full level  
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Citation (search report)  
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• [XYI] US 2003170437 A1 20030911 - KAWASHIMA TAKUYA [JP], et al  
• [XYI] EP 1798774 A2 20070620 - BOEING CO [US]  
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• [XYI] A. CHAOUI ET AL: "Indium tin oxide/(n+-p) silicon solar cell", SOLAR CELLS, vol. 14, no. 2, 1 May 1985 (1985-05-01), pages 133 - 138, XP055026578, ISSN: 0379-6787, DOI: 10.1016/0379-6787(85)90035-3  
• See also references of WO 2009136863A1

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